



2017 International Electron Devices and Materials Symposium

September 6-8, 2017 National Chiao Tung University, Hsinchu, Taiwan

2017 IEDMS開始報名(預先報名截止8/24)

報名網址 <http://iedms2017.nctu.edu.tw/registration.php>



註冊者可以任選只參加short course或IEDMS會議其中一項，或全程參加。

September 6 – Short Course

Course-1: Advanced devices and materials for future CMOS-based IC Technologies

Lecturer: Prof. S. Takagi (University of Tokyo)

High mobility MOSFET Technology

- SiGe/Ge

- III-V semiconductors

3D integration of CMOS

Steep slope devices- Tunneling FET and Negative Capacitance FET

2D materials



Course-2: Embedded Memory Design in CMOS Technology

Lecturer: Dr. Eric Y. Wang (Intel)

CMOS Technology Scaling

Embedded Memory Technologies

- Scaling Trend and Applications

Embedded Memory Design

- Challenges, Circuit Techniques and Reliability

Emerging Embedded Memory

- Technology, applications and status

September 7,8 –IEDMS

Keynote

1. Real Limits to Nanoelectronics - Interconnects and Contacts

Professor Krishna Saraswat, Stanford University

2. Emerging Applications with More-than-More Technologies

Dr. Meikei leong, Hong Kong Applied Science and Technology Research Institute, ASTRI

Invited Talks

More than 15 invited talks in various semiconductor fields

Oral/poster paper presentations

52 oral papers and 130 posters



會議主題領域

- Compound semiconductor materials and devices
化合物半導體材料與元件
- Novel materials, large-area electronics
新穎材料、大面積元件
- Si-based processing, devices and integration
矽基材料、元件與製程整合
- Photovoltaic materials/devices
光伏材料、元件

Exhibition
September 6-8

Web site: <http://iedms2017.nctu.edu.tw/>

